

IN THE SPECIFICATION:

Please insert before the first line in the specification the following new paragraph:

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is a division of U.S. Application No. 09/901,676, filed on July 11, 2001.

Please replace the paragraph beginning on Page 8, line 1, with the following:

As developing solutions not containing silicic acid alkali salt, a developing solution comprising an alkali reagent, a complexing agent, an anionic surfactant, an emulsifying agent, an ~~n-alkane~~ n-alkanoic acid, etc., is disclosed in JP-A-61-109052, and a developing solution comprising an alkali agent, a complexing agent, an anionic surfactant, an amyl alcohol, ~~N-alkoxylamines~~ N-alkoxyamines, etc., is disclosed in West German Patent 1,984,605, but the damage to an image domain is great due to their high pH values and organic solvents contained, and sufficient printing properties, such as press life, cannot be obtained.

Please replace the paragraph beginning on Page 12, line 11, with the following:

(10) A photosensitive lithographic printing plate ~~compring~~ comprising a photopolymerizable photosensitive layer, wherein the photosensitive layer contains a compound having an acid radical having a pKa of 9 or less and the acid value of the photosensitive layer is from 0.20 to 0.60 meq/g.

Please replace the paragraph beginning on Page 21, line 21, with the following:

The substituted alkyl group is made by bonding a substituent with an alkylene group, and monovalent non-metallic atomic groups exclusive of a hydrogen atom are used as the substituents. Preferred examples of the substituents of the substituted alkyl group include a halogen atom (-F, -Br, -Cl, -I), a hydroxyl group, an alkoxyl group, an aryloxy group, a mercapto group, an alkylthio group, an arylthio group, an alkyldithio group, an aryldithio group, an amino group, an N-alkylamino group, an N,N-dialkylamino group, an N-arylamino group, an N,N-diarylamino group, an N-alkyl-N-arylamino group, an acyloxy group, a carbamoyloxy group, an N-alkylcarbamoyloxy group, an N-arylcarbamoyloxy group, an N,N-dialkylcarbamoyloxy group, an N,N-diarylcarbamoyloxy group, an N-alkyl-N-arylcarbamoyloxy group, an alkylsulfoxy group, an arylsulfoxy group, an acylthio group, an acylamino group, an N-alkylacylamino group, an N-arylacylamino group, a ureido group, an N'-alkylureido group, an N',N'-dialkylureido group, an N'-arylureido group, an N',N'-diarylureido group, an N'-alkyl-N'-arylureido group, an N-alkylureido group, an N-arylureido group, an N'-alkyl-N-alkylureido group, an N'-alkyl-N-arylureido group, an N',N'-dialkyl-N-alkylureido group, an N',N'-dialkyl-N-arylureido group, an N'-aryl-N-alkylureido group, an N'-aryl-N-arylureido group, an N',N'-diaryl-N-alkylureido group, an N',N'-diaryl-N-arylureido group, an N'-alkyl-N'-aryl-N-alkylureido group, an N'-alkyl-N'-aryl-N-arylureido group, an alkoxycarbonylamino group, an aryloxycarbonylamino group, an N-alkyl-N-alkoxycarbonylamino group, an N-alkyl-N-aryloxycarbonylamino group, an N-aryl-N-alkoxycarbonylamino group, an

N-aryl-N-aryloxycarbonylamino group, a formyl group, an acyl group, a carboxyl group and a conjugate base group of it (hereinafter referred to as a carboxylato group), an alkoxycarbonyl group, an aryloxy-carbonyl group, a carbamoyl group, an N-alkylcarbamoyl group, an N,N-dialkylcarbamoyl group, an N-arylcarbamoyl group, an N,N-diarylcarbamoyl group, an N-alkyl-N-arylcarbamoyl group, an alkylsulfinyl group, an arylsulfinyl group, an alkyl-sulfonyl group, an arylsulfonyl group, a sulfo group ($-\text{SO}_3\text{H}$) and a conjugate base group of it (hereinafter referred to as a sulfonato group), an alkoxysulfonyl group, an aryloxy-sulfonyl group, a sulfinamoyl group, an N-alkylsulfinamoyl group, an N,N-dialkylsulfinamoyl group, an N-arylsulfinamoyl group, an N,N-diarylsulfinamoyl group, an N-alkyl-N-aryl-sulfinamoyl group, a sulfamoyl group, an N-alkylsulfamoyl group, an N,N-dialkylsulfamoyl group, an N-arylsulfamoyl group, an N,N-diarylsulfamoyl group, an N-alkyl-N-aryl-sulfamoyl group, an N-acylsulfamoyl group and a conjugate base group of it, an N-alkylsulfonylsulfamoyl group ($-\text{SO}_2\text{NHSO}_2(\text{alkyl})$) and a conjugate base group of it, an N-arylsulfonylsulfamoyl group ($-\text{SO}_2\text{NHSO}_2(\text{aryl})$) and a conjugate base group of it, an N-alkylsulfonylcarbamoyl group ($-\text{CONHSO}_2(\text{alkyl})$) and a conjugate base group of it, an N-arylsulfonylcarbamoyl group ($-\text{CONHSO}_2(\text{aryl})$) and a conjugate base group of it, an alkoxysilyl group (~~$-\text{Si}(\text{O-alkyl})_3$~~) ($-\text{Si}(\text{O-alkyl})_3$), an aryloxysilyl group (~~$-\text{Si}(\text{O-aryl})_3$~~) ($-\text{Si}(\text{O-aryl})_3$), a hydroxysilyl group ($-\text{Si}(\text{OH})_3$) and a conjugate base group of it, a phosphono group ($-\text{PO}_3\text{H}_2$) and a conjugate base group of it (hereinafter referred to as a phosphonato group), a dialkylphosphono group ($-\text{PO}_3(\text{alkyl})_2$), a diarylphosphono group ($-\text{PO}_3(\text{aryl})_2$), an alkylarylphosphono group ($-\text{PO}_3(\text{alkyl})(\text{aryl})$), a monoalkyl-phosphono group ($-\text{PO}_3\text{H}(\text{alkyl})$) and a conjugate base group of it (hereinafter

referred to as an alkylphosphonato group), a monoarylphosphono group ($-\text{PO}_3\text{H}(\text{aryl})$) and a conjugate base group of it (hereinafter referred to as an arylphosphonato group), a phosphonooxy group ($-\text{OPO}_3\text{H}_2$) and a conjugate base group of it (hereinafter referred to as a phosphonatooxy group), a dialkylphosphonooxy group ($-\text{OPO}_3(\text{alkyl})_2$), a diarylphosphonooxy group ($-\text{OPO}_3(\text{aryl})_2$), an alkylaryl-phosphonooxy group ($-\text{OPO}_3(\text{alkyl})(\text{aryl})$), a monoalkyl-phosphonooxy group ($-\text{OPO}_3\text{H}(\text{alkyl})$) and a conjugate base group of it (hereinafter referred to as an alkylphosphonatooxy group), a monoarylphosphonooxy group ($-\text{OPO}_3\text{H}(\text{aryl})$) and a conjugate base group of it (hereinafter referred to as an arylphosphonatooxy group), a cyano group, a nitro group, an aryl group, an alkenyl group, and an alkynyl group.

Please replace the paragraph beginning on page 66, line 17, with the following:

By introducing radical reactive groups into the side chain of these high polymers, the strength of the cured film can be improved. A group having an ethylenically unsaturated bond, an amino group and an epoxy group can be exemplified as an addition polymerization reactive functional group, a mercapto group, a thiol group, a halogen atom, a triazine structure and an onium structure can be exemplified as a functional group capable of becoming a radical by irradiation, and a carboxyl group and an imido group can be exemplified as a polar group. As the above addition polymerization reactive functional group, a group having an ethylenically unsaturated bond, e.g., an acryl group, a methacryl group, an allyl group, and a styrene group, is particularly preferred, but functional groups selected from among an amino group, a hydroxyl group, a phosphonic acid group, a

phosphoric acid group, a carbamoyl group, an isocyanate group, a ureido group, a ureylene group, a sulfonic acid group and an ~~ammonio~~ ammonium group are also useful.

Please replace the paragraph beginning on page 84, line 18, with the following:

As other exposure rays, a mercury lamp of ultra-high pressure, high pressure, intermediate pressure and low pressure, a chemical lamp, a carbon arc lamp, a xenon lamp, a metal halide lamp, and various ultraviolet laser lamps (e.g., ArF ~~eximer~~ excimer laser, KrF ~~eximer~~ excimer laser, etc.), a halogen lamp, a fluorescent lamp, a tungsten lamp, and as radiation, electron rays, X-rays, ion beams, far infrared rays can also be used. The above laser light sources of 350 nm or more are particularly preferred in the point of inexpensiveness.

Please replace the paragraph beginning on page 87, line 10, with the following:

A 1S aluminum plate having a thickness of 0.30 mm was subjected to brush-graining treatment using a No. 8 nylon brush and a suspension of 800 mesh ~~pumice~~ pumice ~~stone~~ and water, and the surface of the plate was thoroughly washed with water. The etching was effected by immersing the plate in a 10% sodium hydroxide aqueous solution at 70°C for 60 seconds, the plate was further washed with flowing water, then washed with a 20% HNO₃ aqueous solution for neutralization followed by washing with water. Under the condition of V_A of 12.7 V using alternating waveform electric current of sine wave, the plate was subjected to electrolytic surface roughening treatment in a 1% nitric acid aqueous solution by the quantity of electricity of 300 C/dm² at anode. The

surface roughness measured was $0.45\ \mu\text{m}$ (Ra). Subsequently, the plate was immersed in a 30% H_2SO_4 aqueous solution and desmutting treatment was performed at 55°C for 2 minutes. Then, the cathode was arranged on the surface having been subjected to graining treatment in a 20% H_2SO_4 aqueous solution at 33°C , and the plate was anodized at electric current density of $5\text{A}/\text{dm}^2$ for 50 seconds. The anodic oxidation layer obtained had a thickness of $2.7\ \text{g}/\text{m}^2$. This plate was designated support 1.

Please replace the paragraph beginning on page 107, line 11, with the following:

A 1S aluminum plate having a thickness of 0.30 mm was subjected to brush-graining treatment using a No. 8 nylon brush and a suspension of 800 mesh ~~pumice~~ pumice stone and water, and the surface of the plate was thoroughly washed with water. The etching was effected by immersing the plate in a 10% sodium hydroxide aqueous solution at 70°C for 60 seconds, the plate was further washed with flowing water, then washed with a 20% HNO_3 aqueous solution for neutralization followed by washing with water. Under the condition of V_A of 12.7 V using alternating waveform electric current of sine wave, the plate was subjected to electrolytic surface roughening treatment in a 1% nitric acid aqueous solution by the quantity of electricity of $300\ \text{C}/\text{dm}^2$ at anode. The surface roughness determined was $0.45\ \mu\text{m}$ (Ra). Subsequently, the plate was immersed in a 30% H_2SO_4 aqueous solution and desmutting treatment was performed at 55°C for 2 minutes. Then, the cathode was arranged on the surface having been subjected to graining treatment in a 20% H_2SO_4 aqueous solution at 33°C , and the plate was anodized at electric

current density of 5A/dm^2 for 50 seconds. The anodic oxidation layer obtained had a thickness of 2.7 g/m^2 .

Please replace the paragraph beginning on page 113, line 13, with the following:

A lithographic printing plate was in the same manner as in Example (1) except that ~~ethylenically~~ ethylenically unsaturated compound A1 in photopolymerizable composition 1 in Example (1) was changed to the following A2.